

FAST RECOVERY RECTIFIER DIODES

- SOFT RECOVERY
- VERY HIGH VOLTAGE
- SMALL RECOVERY CHARGE


F 126

(Plastic)

APPLICATIONS

- ANTISATURATION DIODES FOR TRANSISTOR BASE DRIVE
- SNUBBER DIODES

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
$I_{F_{RM}}$	Repetitive Peak Forward Current	20	A
I_F (AV)	Average Forward Current*	1	A
I_{FSM}	Surge non Repetitive Forward Current	35	A
P_{tot}	Power Dissipation*	1.25	W
T_{stg} T_j	Storage and Junction Temperature Range	- 55 to 150	°C
T_L	Maximum Lead Temperature for Soldering during 10s at 4mm from Case	230	°C

Symbol	Parameter	BYT 11-			Unit
		600	800	1000	
V_{RRM}	Repetitive Peak Reverse Voltage	600	800	1000	V

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R_{th} (j-a)	Junction-ambient*	60	°C/W

* On infinite heatsink with 10mm lead length

ELECTRICAL CHARACTERISTICS**STATIC CHARACTERISTICS**

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I_R	$T_j = 25^\circ C$	$V_R = V_{RRM}$			20	μA
V_F	$T_j = 25^\circ C$	$I_F = 1A$			1.3	V

RECOVERY CHARACTERISTICS

Symbol	Test Conditions				Min.	Typ.	Max.	Unit
t_{rr}	$T_j = 25^\circ C$	$I_F = 0.5A$	$I_R = 1A$	$I_{rr} = 0.25A$			100	ns

To evaluate the conduction losses use the following equations :

$$V_F = 1.1 + 0.075 I_F \quad P = 1.1 \times I_F(AV) + 0.075 \times I_F^2(RMS)$$

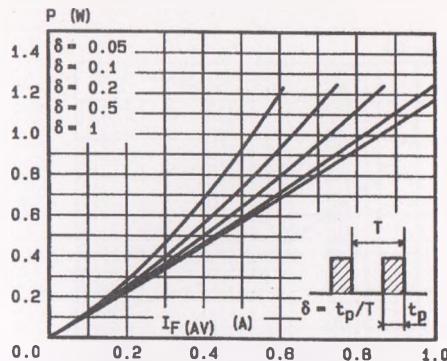


Fig.1 - Maximum average power dissipation versus average forward current.

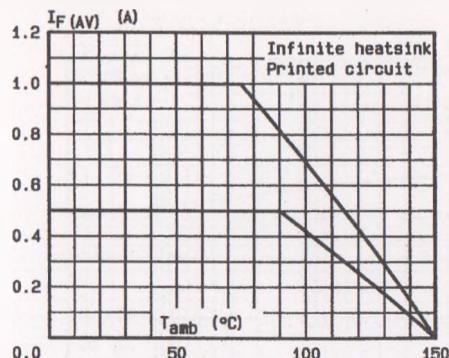


Fig.2 - Average forward current versus ambient temperature.

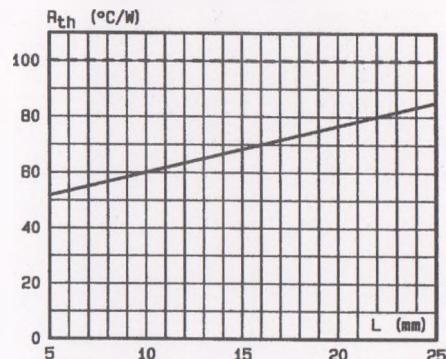


Fig.3 - Thermal resistance versus lead length.

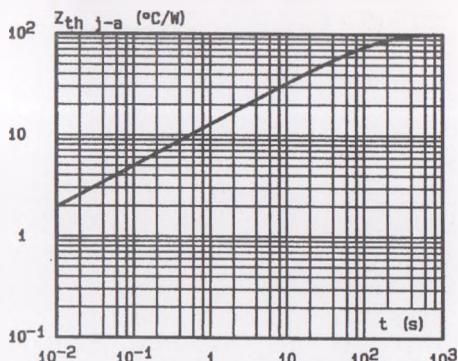


Fig.4 - Transient thermal impedance junction-ambient for mounting n°2 versus pulse duration ($L = 10$ mm).

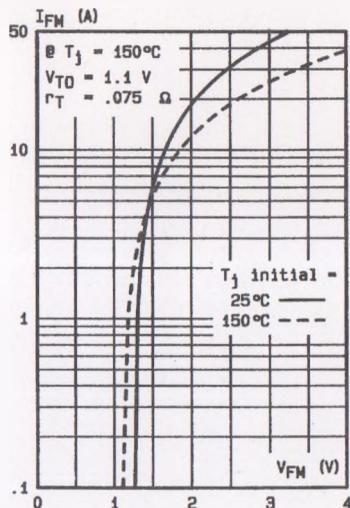
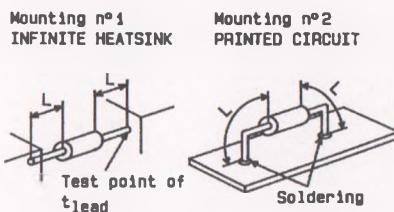


Fig.5 - Peak forward current versus peak forward voltage drop (maximum values).

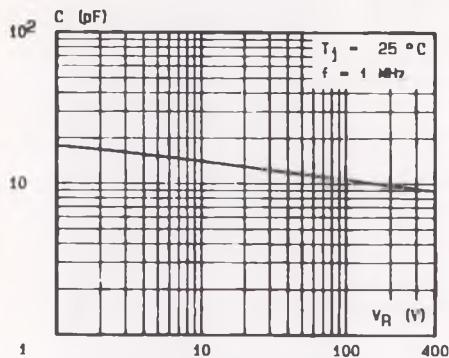


Fig.6 - Capacitance versus reverse applied voltage

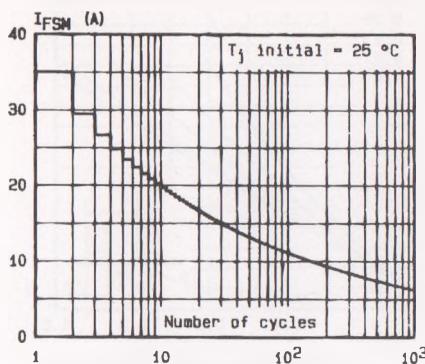


Fig.7 - Non repetitive surge peak current versus number of cycles